

# 深圳市晶泰源电子有限公司

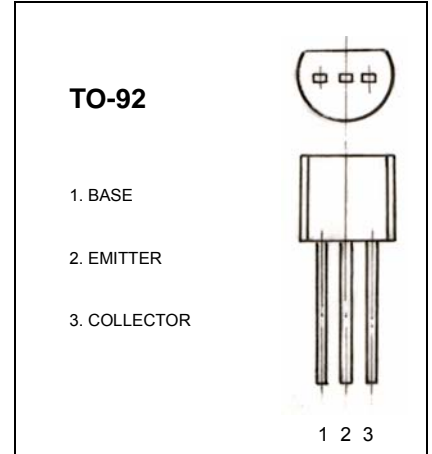
## 2SC2216 TRANSISTOR (NPN)

### FEATURES

Amplifier dissipation NPN Silicon

### MAXIMUM RATINGS ( $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	50	V
$V_{CEO}$	Collector-Emitter Voltage	45	V
$V_{EBO}$	Emitter-Base Voltage	4	V
$I_C$	Collector Current -Continuous	50	mA
$P_C$	Collector Dissipation	300	mW
$T_J$	Junction Temperature	125	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55-125	$^{\circ}\text{C}$



### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	4			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=50\text{V}, I_E=0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=3\text{V}, I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=12.5\text{V}, I_C=12.5\text{mA}$	40		140	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=15\text{mA}, I_B=1.5\text{mA}$			0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=15\text{mA}, I_B=1.5\text{mA}$			1.5	V
Transition frequency	$f_T$	$V_{CE}=12.5\text{V}, I_C=12.5\text{mA}$	300			MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=30\text{MHz}$			2.0	pF